



30V N-Channel Enhancement Mode MOSFET- ESD Protected

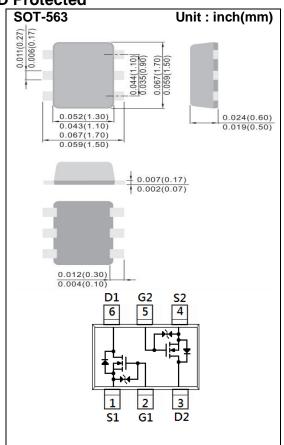
Voltage 30 V Current 350mA

Features

- RDS(ON) , VGS@4.5V, ID@350mA<1.2Ω
- RDS(ON) , VGS@2.5V, ID@200mA<1.6Ω
- RDS(ON) , VGS@1.8V, ID@80mA<2.3Ω
- RDS(ON), VGS@1.5V, ID@10mA<2.5Ω(typ.)
- Advanced Trench Process Technology
- ESD Protected 2KV HBM
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: SOT-563 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00009 ounces, 0.0026 grams
- Marking: X12



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V_{GS}	<u>+</u> 10	V
Continuous Drain Current		I _D	350	mA
Pulsed Drain Current (Note 1)		I _{DM}	1400	mA
Power Dissipation	T _A =25°C	P _D	300	mW
	Derate above 25°C		2.4	mW/°C
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Typical Thermal resistance - Junction to Ambient (Note 3)		$R_{\theta JA}$	417	°C/W





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	0.6	0.85	1.1	V		
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =4.5V, I_{D} =350mA	-	0.94	1.2	Ω		
		V_{GS} =2.5V, I_D =200mA	-	1.32	1.6			
		V_{GS} =1.8V, I_D =80mA	-	1.82	2.3			
		V_{GS} =1.5V, I_D =10mA	-	2.5	-			
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =30V, V_{GS} =0V	-	0.01	1	uA		
Gate-Source Leakage Current	I _{GSS}	$V_{GS}=\underline{+}8V, V_{DS}=0V$	-	-	<u>+</u> 10	uA		
		$V_{GS}=\underline{+}5V, V_{DS}=0V$	-	-	<u>+</u> 1			
Dynamic (Note 5)								
Total Gate Charge	Q_g	V_{DS} =15V, I_{D} =350mA, V_{GS} =4.5V (Note 1,2)	-	0.87	-	nC		
Gate-Source Charge	Q_gs		-	0.26	-			
Gate-Drain Charge	Q_gd		-	0.16	-			
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V, f=1.0MHZ	-	34	-	pF		
Output Capacitance	Coss		-	8.9	-			
Reverse Transfer Capacitance	Crss	I=1.UIVITZ	-	2.5	-			
Turn-On Delay Time	td _(on)	\/ 45\/ 00m A	-	7.1	-	ns		
Turn-On Rise Time	tr	V_{DD} =15V, I_{D} =80mA, V_{GS} =4.0V, R_{G} =6 Ω (Note 1,2)	-	20	-			
Turn-Off Delay Time	td _(off)		-	41	-			
Turn-Off Fall Time	tf	K _G =012	-	31	-			
Drain-Source Diode								
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	350	mA		
Diode Forward Voltage	V_{SD}	I _S =350mA, V _{GS} =0V	-	0.88	1.3	V		

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited
- 5. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

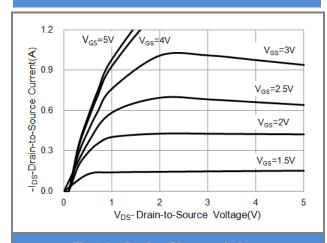


Fig.1 On-Region Characteristics

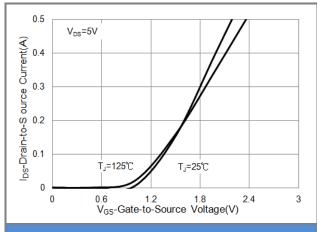


Fig.2 Transfer Characteristics

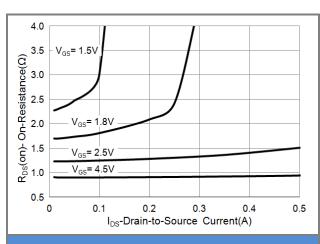


Fig.3 On-Resistance vs. Drain Current

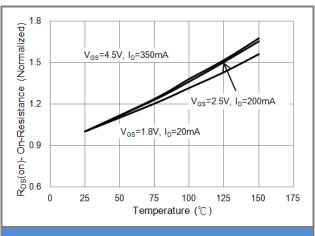


Fig.4 On-Resistance vs. Junction temperature

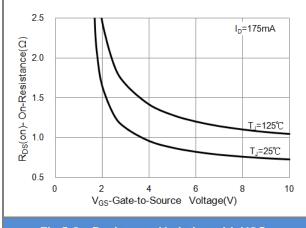


Fig.5 On-Resistance Variation with VGS.

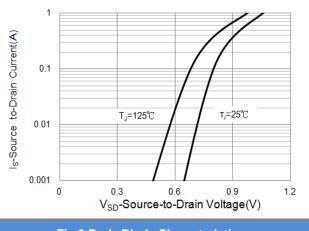


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

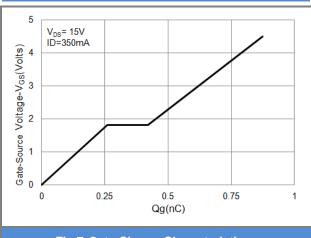


Fig.7 Gate-Charge Characteristics

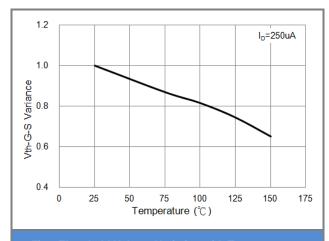


Fig.8 Threshold Voltage Variation with Temperature.

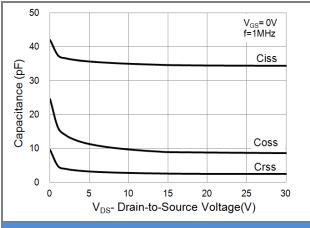


Fig.9 Capacitance vs. Drain-Source Voltage.

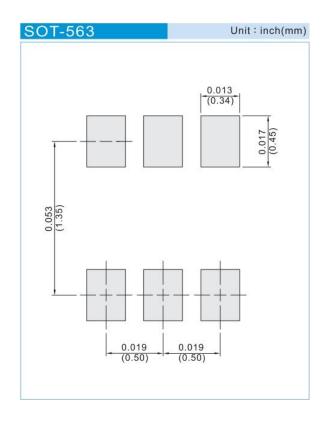




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJX8812_R1_00001	SOT-563	4K pcs / 7" reel	X12	Halogen free
PJX8812_R2_00001	SOT-563	10K pcs / 13" reel	X12	Halogen free
PJX8812_R1_00002	SOT-563	8K pcs / 7" reel	X12	Halogen free
PJX8812_R2_00002	SOT-563	20K pcs / 13" reel	X12	Halogen free

MOUNTING PAD LAYOUT







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